

# E.S.D NOISE CLIPPING DIODES NNCD3.3F to NNCD12F

# ELECTROSTATIC DISCHARGE NOISE CLIPPING DIODES (DOUBLE TYPE, ANODE COMMON) 3PIN MINI MOLD

This product series is a diode developed for E.S.D (Electrostatic Discharge) noise protection. Based on the IEC1000-4-2 test on electromagnetic interference (EMI), the diode assures an endurance of no less than 30 kV, thus making itself most suitable for external interface circuit protection.

Type NNCD3.3F to NNCD12F Series include two elements in 3PIN Mini Mold Package having allowable power dissipation of 200 mW.

#### **FEATURES**

- Based on the electrostatic discharge immunity test (IEC1000-4-2), the product assures the minimum endurance of 30 kV.
- Based on the reference supply of the set, the product achieves a series over a wide range (15 product name lined up).

#### **APPLICATIONS**

- · External interface circuit E.S.D protection.
- · Circuits for Waveform clipper, Surge absorber.

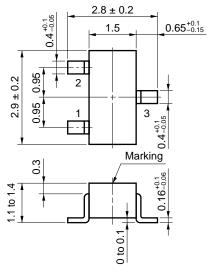
#### MAXIMUM RATINGS ( $T_A = 25$ °C)

Power Dissipation P 200 mW (Total) Surge Reverse Power PRSM 100 W (tT = 10  $\mu$ s 1 pulse) Fig. 6 Junction Temperature T<sub>j</sub> 150 °C

Storage Temperature T<sub>stg</sub> -55 °C to +150 °C

#### PACKAGE DIMENSIONS

(in millimeters)

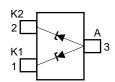


#### PIN CONNECTION

1. K1: Cathode 1 SC-59 (EIAJ)

2. K2: Cathode 2

3. A: Anode (common)





# ELECTRICAL CHARACTERISTICS (TA = 25 $^{\circ}$ C) (A-K1, A-K2)

Type Number	Breakdown Voltage <sup>Note</sup> 1 V <sub>BR</sub> (V)			Dynamic Impedance <sup>Note 2</sup> Zz (Ω)		Reverse Leakage I <sub>R</sub> (µA)		Capacitance C <sub>1</sub> (pF)		E.S.D Voltage (kV)	
	MIN.	MAX.	Iτ (mA)	MAX.	Iτ (mA)	MAX.	V <sub>R</sub> (V)	TYP.	TEST CONDITION	MIN.	TEST CONDITION
NNCD3.3F	3.10	3.50	5	130	5	20	1.0	220	VR = 0 V f = 1 MHz	30	C = 150 pF R = 330 Ω (IEC1000 -4-2)
NNCD3.6F	3.40	3.80	5	130	5	10	1.0	210		30	
NNCD3.9F	3.70	4.10	5	130	5	10	1.0	200		30	
NNCD4.3F	4.01	4.48	5	130	5	10	1.0	180		30	
NNCD4.7F	4.42	4.90	5	130	5	10	1.0	170		30	
NNCD5.1F	4.84	5.37	5	130	5	5	1.5	160		30	
NNCD5.6F	5.31	5.92	5	80	5	5	2.5	140		30	
NNCD6.2F	5.86	6.53	5	50	5	2	3.0	120		30	
NNCD6.8F	6.47	7.14	5	30	5	2	3.5	110		30	
NNCD7.5F	7.06	7.84	5	30	5	2	4.0	90		30	
NNCD8.2F	7.76	8.64	5	30	5	2	5.0	90		30	
NNCD9.1F	8.56	9.55	5	30	5	2	6.0	90		30	
NNCD10F	9.45	10.55	5	30	5	2	7.0	80		30	
NNCD11F	10.44	11.56	5	30	5	2	8.0	70		30	
NNCD12F	11.42	12.60	5	35	5	2	9.0	70		30	

Notes 1. Tested with pulse (40 ms)

2. Zz is measured at I<sub>T</sub> give a small A.C. signal.

#### TYPICAL CHARACTERISTICS (TA = 25 °C)

Fig. 1 POWER DISSIPATION vs. AMBIENT TEMPERATURE

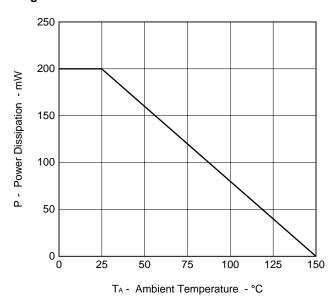


Fig. 2 IT - VBR CHARACTERISTICS

NNCD7.5F NNCD8.2F NNCD6.8F NNCD9.1F 100 m NNCD3.3F NNCD3.3F NNCD3.9F NNCD4.3F 10 m - On State Current - A 100 π 100 μ M NNCD4.7  $1 \mu$ NNCD5.1F 100 n NNCD5.6F 10 n 1 n 🗀 2 3 4 5 6 7 8 9 10 V<sub>BR</sub> - Breakdown Voltage - V

Fig. 3 IT - VBR CHARACTERISTICS

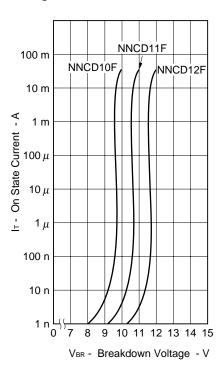


Fig. 4 Zz - IT CHARACTERISTICS

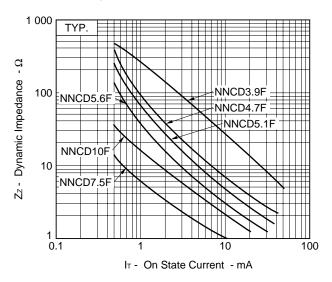


Fig. 5 TRANSIENT THERMAL IMPEDANCE

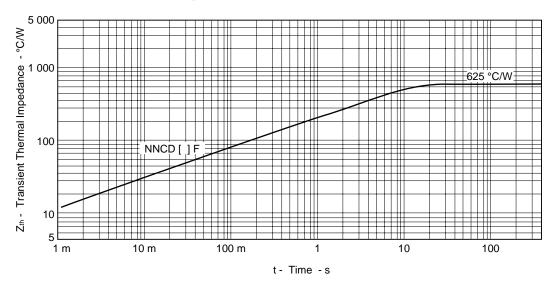
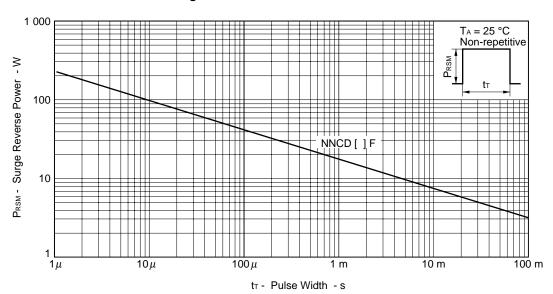
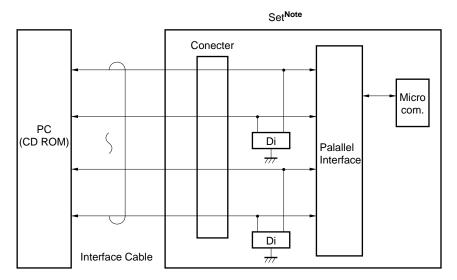


Fig. 6 SURGE REVERSE POWER RATING



## **Sample Application Circuits**



Note Set Printer, P.D.C, T.V Game etc.



## REFERENCE

Document Name	Document No.		
NEC semiconductor device reliability/quality control system	C11745E		
NEC semiconductor device reliability/quality control system	MEI-1201		
Quality grade on NEC semiconductor device	C11531E		
Semiconductor device mounting technology manual	C10535E		
Guide to quality assurance for semiconductor device	MEI-1202		

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Anti-radioactive design is not implemented in this product.